



MOS FET  
 MTM78E2B0LBF

# MTM78E2B0LBF

## Gate Resistor installed Dual N-Channel MOS Type

For lithium-ion secondary battery protection circuit

■ Features

- Low drain-source On-state Resistance  
 RDS(on) typ. = 21.5 mΩ (VGS = 4.0 V)
- Halogen-free / RoHS compliant  
 (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 5A

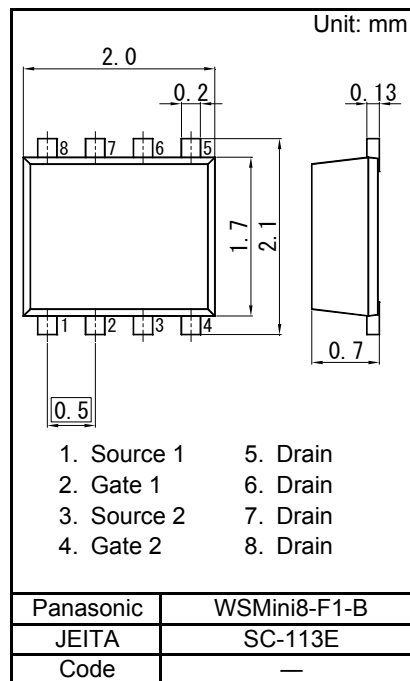
■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

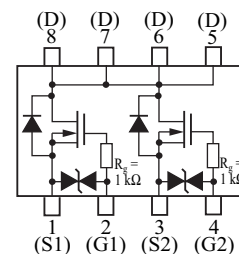
Parameter		Symbol	Rating	Unit
FET1	Drain-source Voltage	VDS	20	V
	Gate-source Voltage	VGS	±12	V
FET2	Drain current	ID	4.0	A
	Peak drain current *1	IDp	40	A
Overall	Total power dissipation	PD1 *2	700	mW
		PD2 *3	150	
Overall	Channel temperature	Tch	150	°C
	Operating ambient temperature	Topr	-40 to +85	°C
	Storage temperature	Tstg	-55 to +150	°C

- Note) \*1 t = 10 μs, Duty Cycle < 1 %  
 Ceramic substrate (70 × 70 × t 1.0 mm)  
 \*2 Dual operating  
 \*3 Stand-alone (without the substrate)



- |             |          |
|-------------|----------|
| 1. Source 1 | 5. Drain |
| 2. Gate 1   | 6. Drain |
| 3. Source 2 | 7. Drain |
| 4. Gate 2   | 8. Drain |

Internal Connection



Pin Name

- |             |          |
|-------------|----------|
| 1. Source 1 | 5. Drain |
| 2. Gate 1   | 6. Drain |
| 3. Source 2 | 7. Drain |
| 4. Gate 2   | 8. Drain |



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■ Electrical Characteristics Ta = 25°C ± 3°C

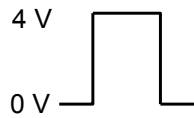
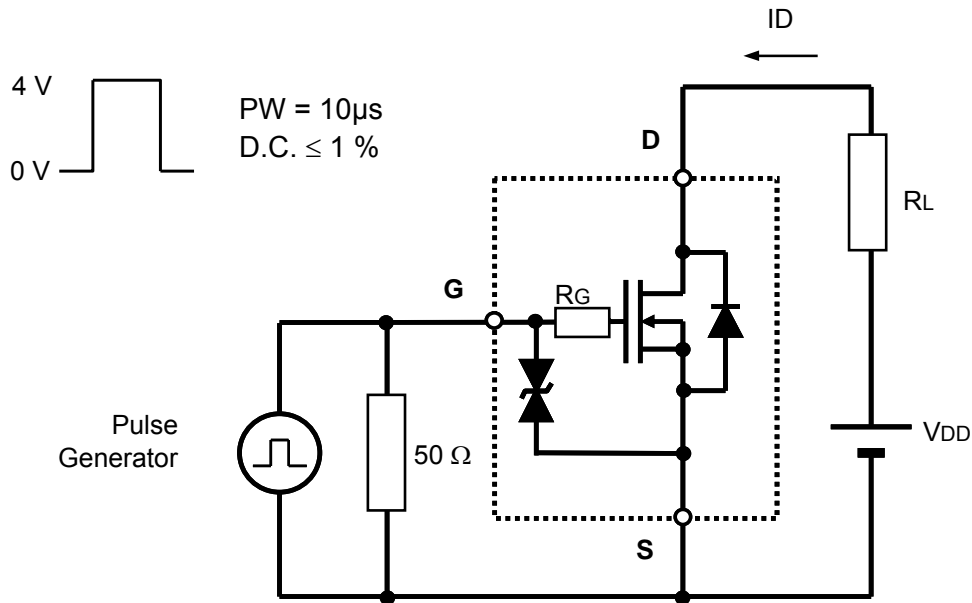
Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Drain-source surrender voltage	VDSS	ID = 1.0 mA, VGS = 0	20			V	
Drain-source cutoff current	IDSS	VDS = 20 V, VGS = 0			1.0	μA	
Gate-source cutoff current	IGSS	VGS = ±12 V, VDS = 0			±10	μA	
Gate threshold voltage	Vth	ID = 1.0 mA, VDS = 10 V	0.40	0.85	1.30	V	
Drain-source ON resistance	RDS(ON)1	ID = 2.0 A, VGS = 4.0 V		21.5	25.0	mΩ	
	RDS(ON)2	ID = 1.5 A, VGS = 3.0 V		26.0	30.0	mΩ	
	RDS(ON)3	ID = 1.0 A, VGS = 2.5 V		30.0	36.0	mΩ	
Forward transfer admittance	Yfs	ID = 1.0 A, VDS = 10 V	1.0			S	
Short-circuit input capacitance (Common source)	Ciss	VDS = 10 V, VGS = 0, f = 1 MHz		1100		pF	
Short-circuit output capacitance (Common source)	Coss			75		pF	
Reverse transfer capacitance (Common source)	Crss			70		pF	
Turn-on delay time <sup>*1, *2</sup>	td(on)				0.2		μs
Rise time <sup>*1, *2</sup>	tr	VDD = 10 V, VGS = 4 V,			0.5		μs
Turn-off delay time <sup>*1, *2</sup>	td(off)	ID = 1.0 A, RL = 10 Ω			2.0		μs
Fall time <sup>*1, *2</sup>	tf				1.5		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

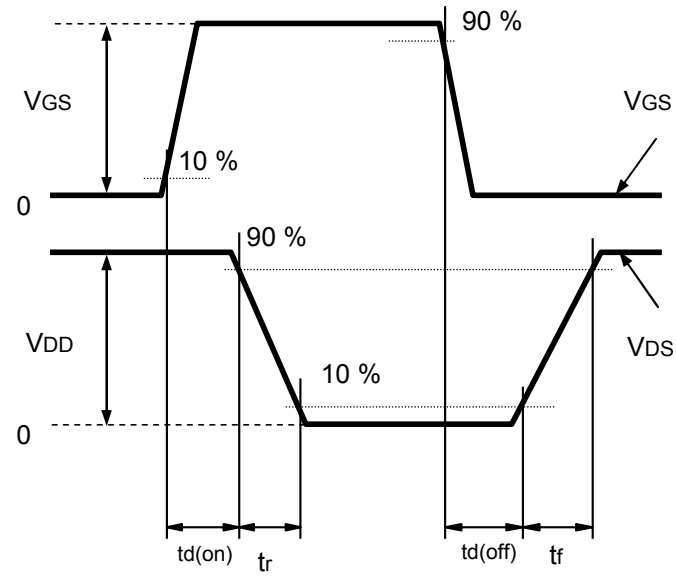
2. \*1 t = 10 μs, Duty Cycle < 1 %

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



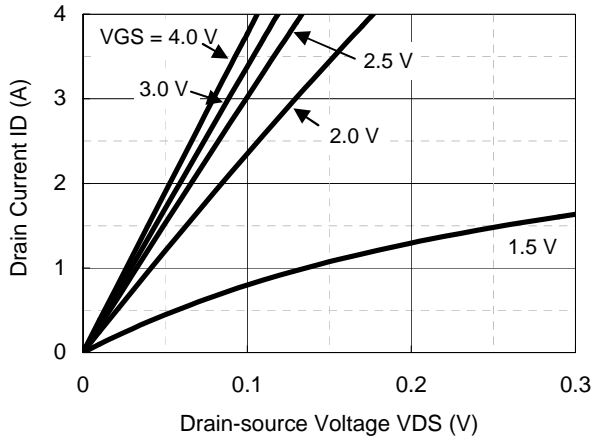
PW = 10 $\mu$ s  
D.C.  $\leq$  1 %



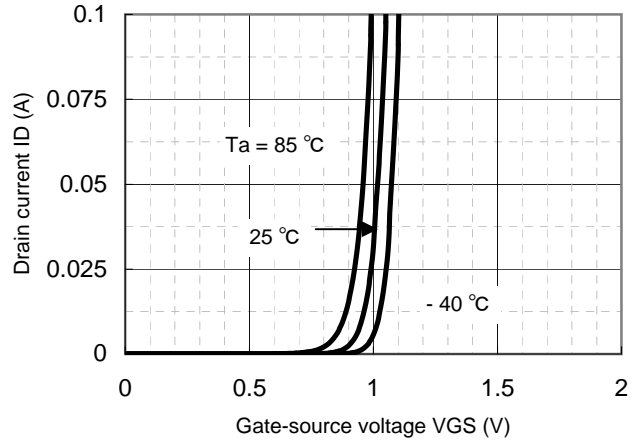


Technical Data ( reference )

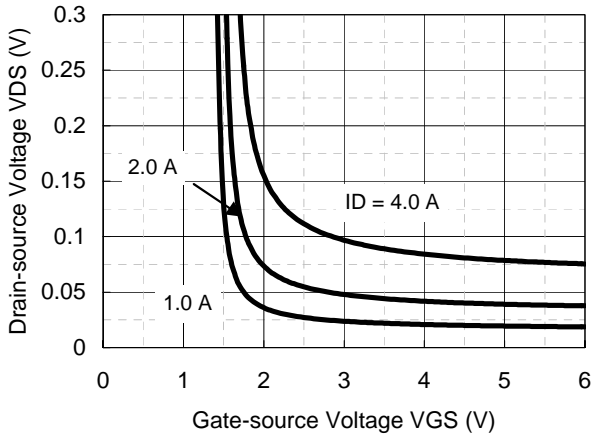
ID - VDS



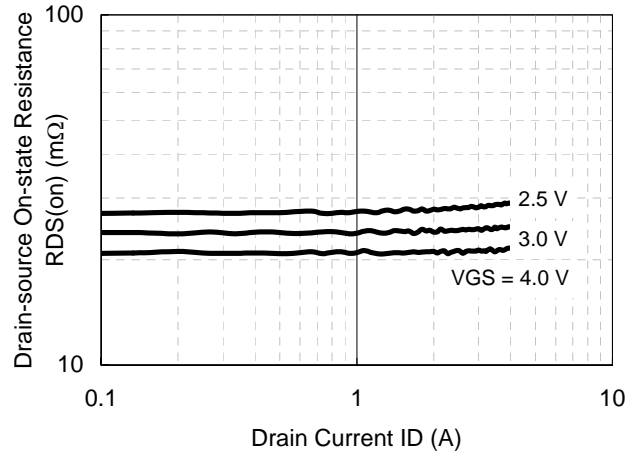
ID - VGS



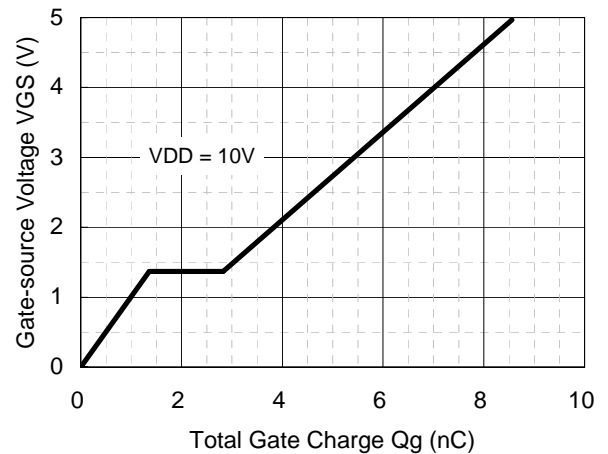
VDS - VGS



RDS(on) - ID

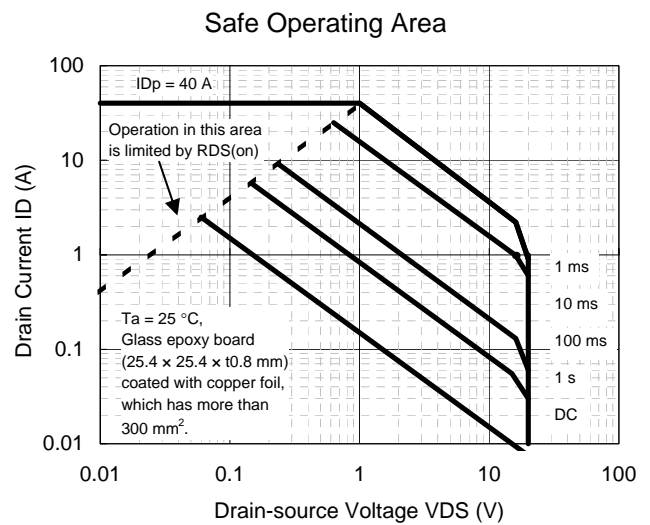
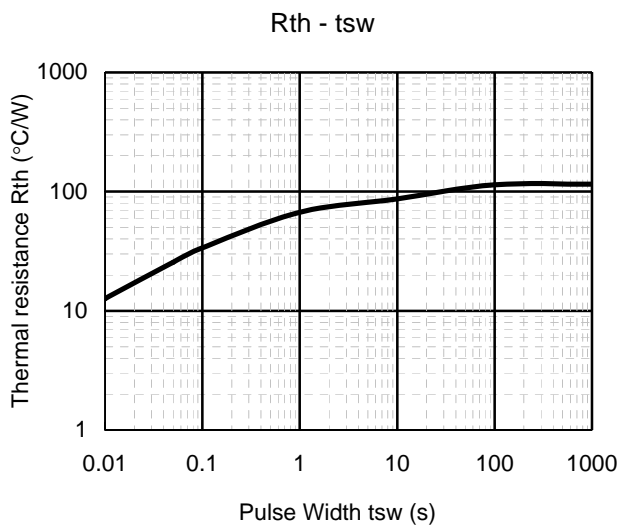
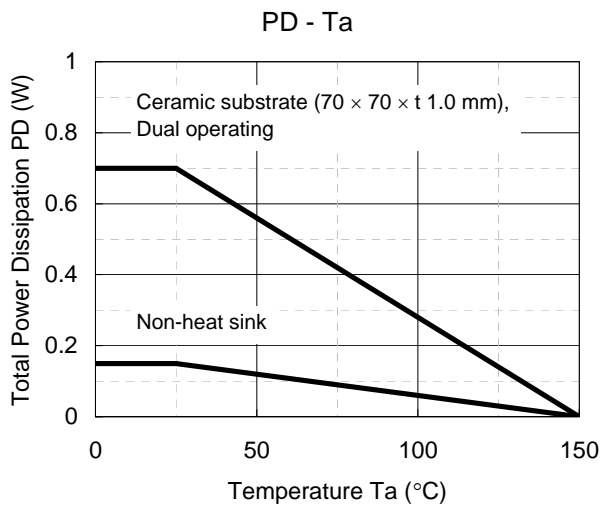
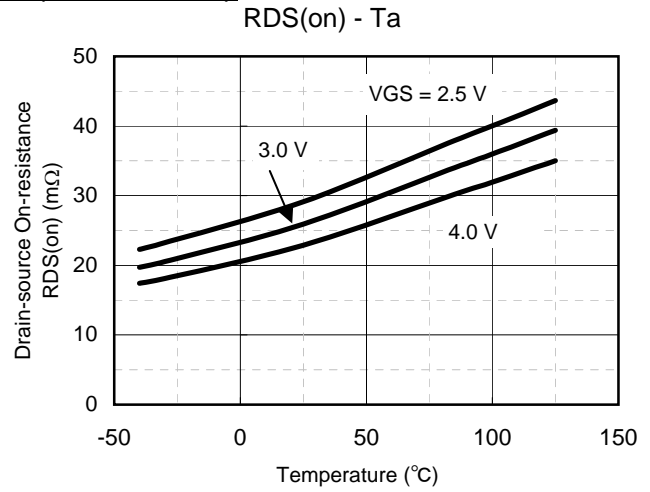
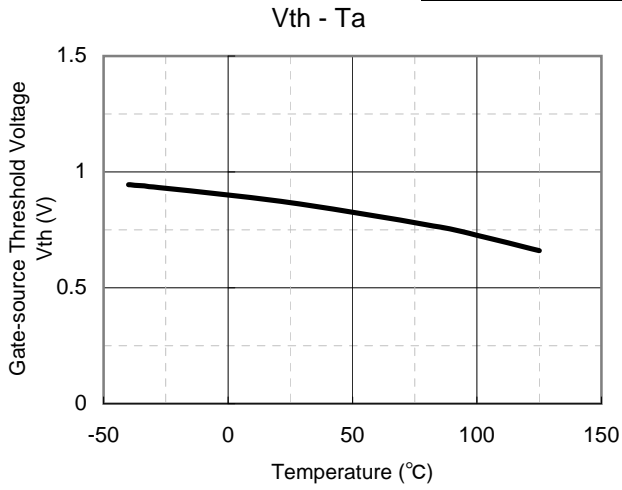


Dynamic Input/Output Characteristics





Technical Data ( reference )

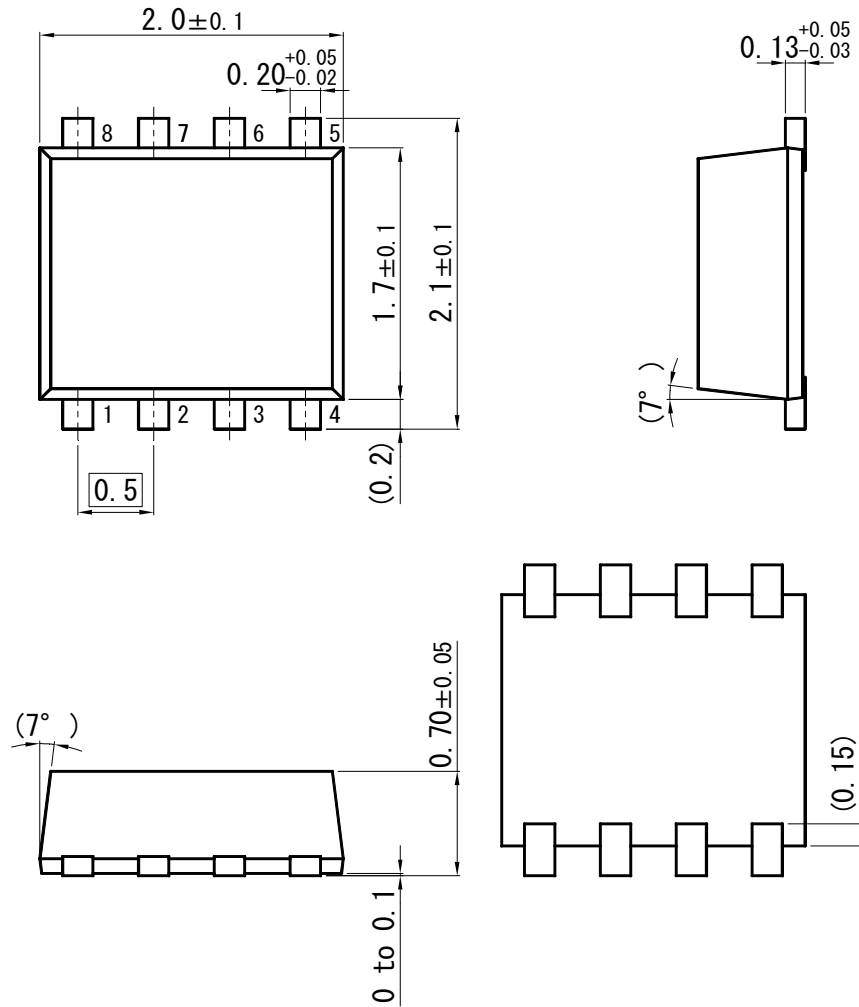




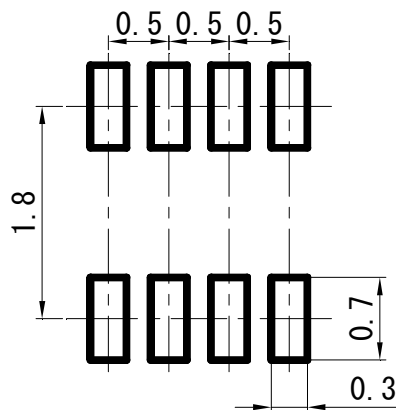
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WSMini8-F1-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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